

Abstract of the Disclosure

The present invention relates to a method for fabricating an image sensor capable of improving a dark current characteristic. The method includes the steps of: forming sequentially a pad oxide layer and a pad nitride layer on a substrate and selectively removing the pad oxide layer and the pad nitride layer to expose a surface of the substrate in which a field insulation layer will be formed; 10 forming the field insulation layer by performing a channel stop ion-implantation process to the exposed substrate with use of the pad nitride layer as a mask; removing a partial portion of the pad nitride layer so that one side of the pad nitride layer is spaced out with a predetermined 15 distance from an edge of the field insulation layer; and performing an additional ion-implantation process onto the exposed substrate surface and the field insulation layer by using the pad nitride layer as a mask.